## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Christopher W. Hill

Serial No.:

Filed: May 19, 2004

For: SILICON NANOCRYSTAL CAPACITOR AND

PROCESS FOR FORMING SAME

Group Art Unit:

Examiner:

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Atty. Docket: 2001-0827.01/US

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Paper No.

## INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

"EXPRESS MAIL" MAILING LABEL NUMBER: <u>ET658403000US</u>
DATE OF DEPOSIT <u>May 19, 2004</u>
IL HERERY CERTISY THAT THIS PAPER IS REING DEPOSITED.

I HEREBY CERTIFY THAT THIS PAPER IS BEING DEPOSITED WITH THE UNITED STATES POSTAL SERVICE "EXPRESS MAIL POST OFFICE TO ADDRESSEE" SERVICE UNDER 37 C.F.R § 1.10 ON THE DATE INDICATED ABOVE AND IS ADDRESSED TO COMMISSIONER FOR PATENTS, P.O. BOX 1450, ALEXANDRIA, VA

22313-1450. Signature

In compliance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant respectfully requests that this Information Disclosure Statement be entered and that the references listed on the attached Form PTO-1449 be considered by the Examiner and made of record. Copies of the listed references are enclosed for the convenience of the Examiner.

In accordance with 37 C.F.R. § 1.97(g), this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possible material information as defined in 37 C.F.R. § 1.56(a) exists.

The following references are submitted for the Examiner's review:

## Other References

"Synthese and characterization of aerosol silicon nanocrystal nonvolatile floating-gate memory device", M.L. Ostraat et al., Applied Physics Letters, Volume 79, Number 3, July 16, 2001, pages 433-435.

"Ultraclean Two-Stage Aerosol Reactor for Production of Oxide-Passivated Silicon Nanoparticles for Novel Memory Devices", Michele L. Ostraat et al., Journal of The Electrochemical Society, 148 (5), Pages G265-G270

As this information is being submitted within three months of the date of filing of the application, Applicant understands that no fee or certification is required for the submission and consideration of this information at this time.

If there are any matters which may be resolved or clarified through telephone interview, the Examiner is respectfully requested to contact Applicant's undersigned agent at the number indicated.

A Form PTO-1449 is enclosed herewith.

Date: 05/19/2004

Respectfully submitted,

David J. Paul

Reg. No. 34,692

Micron Technology, Inc.

8000 S. Federal Way

Boise, ID 83706-9632

(208) 368-4515

AGENT FOR APPLICANT

(REV: 7-80) PATENT AND TRADEMARK OFFICE  INFORMATION DISCLOSURE STATEMENT BY APPLICANT    Christopher W. Hill   Filing Date: Group:	FORM: PT	D-1449	U.S. DEPARTMENT OF COMMERC				Atty Dock	tet No:	Serial No:		
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication with applicant.